P60B4EL

Power MOSFETs 40V, 60A, N-channel

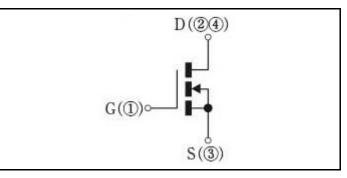
Feature

- N-channel
- SMD
- Low Ron
- 4.5V Gate Drive
- · Low Capacitance
- Pb free terminal
- RoHS:Yes

OUTLINE



Equivalent circuit



Absolute Maximum Ratings (unless otherwise specified : Tc=25°C)

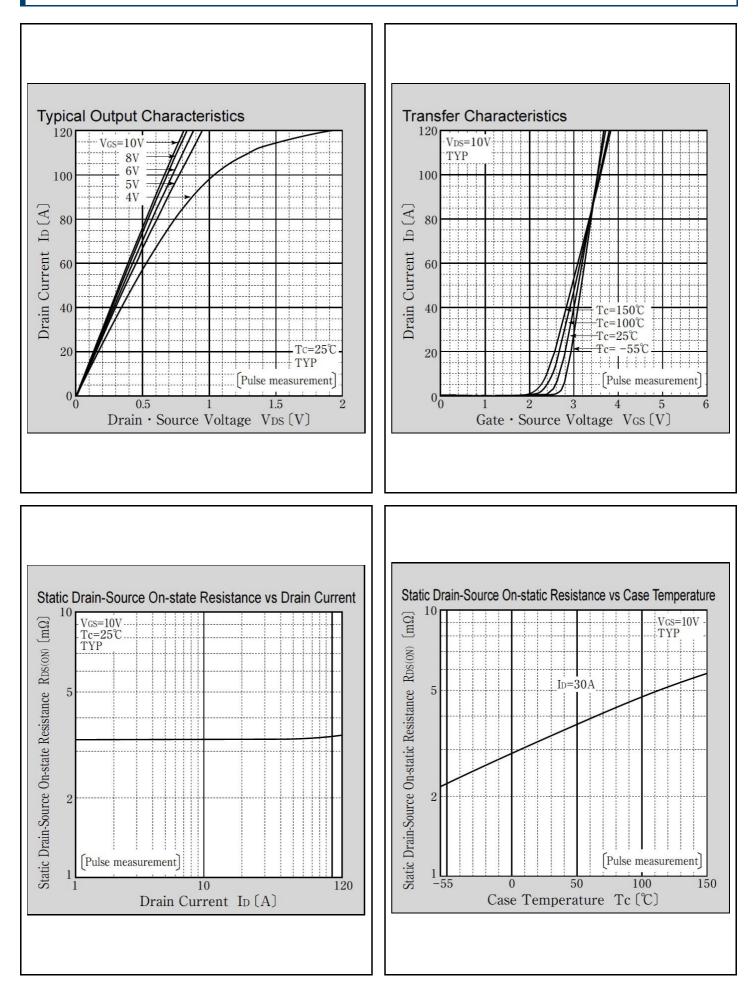
Item	Symbol	Conditions	Ratings	Unit
Storage temperature	Tstg		-55 to 150	°C
Channel tempertature	Tch		150	°C
Drain-source voltage	V _{DSS}		40	V
Gate-source voltage	V _{GSS}		±20	V
Continuous drain current(DC)	I _D		60	Α
Continuous drain current(Peak) I _{DP}		Pulse width 10µs, duty=1/100	240	А
Total power dissipation	P _T		62.5	W
Single avalanche current	I _{AS}	Starting Tch=25°C Tch≦150°C	40	А
Single avalanche energy E _{AS}		Starting Tch=25°C Tch≦150°C	175	mJ

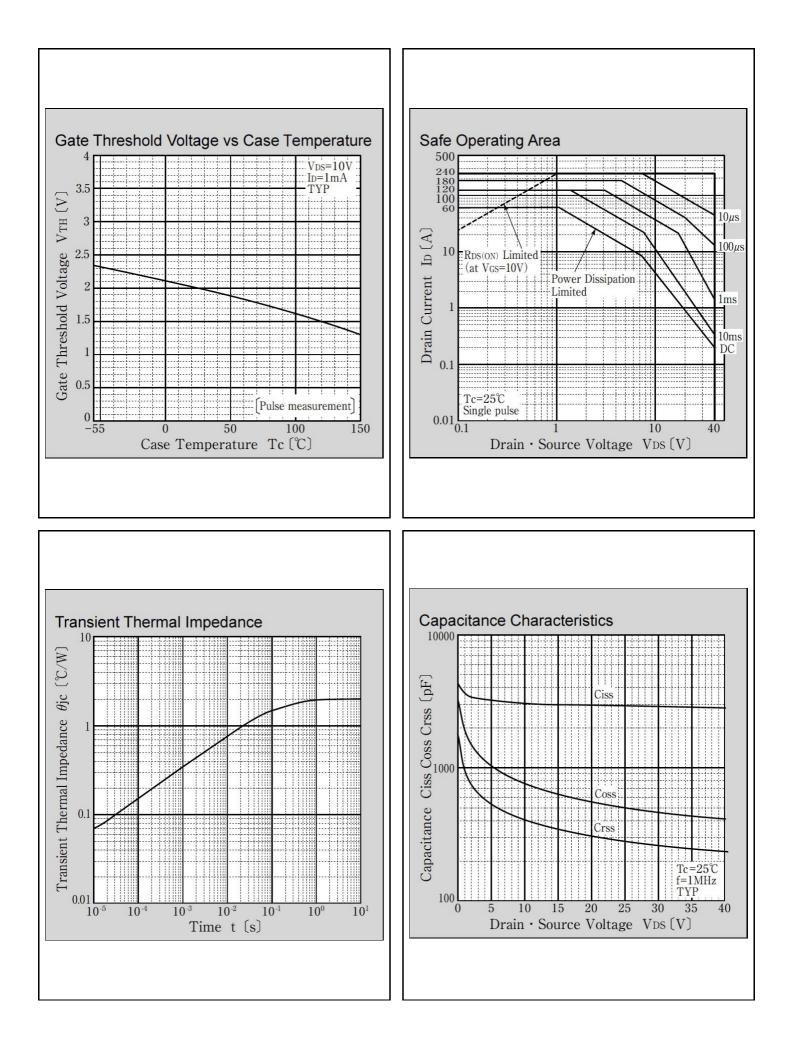
* : See the original Specifications

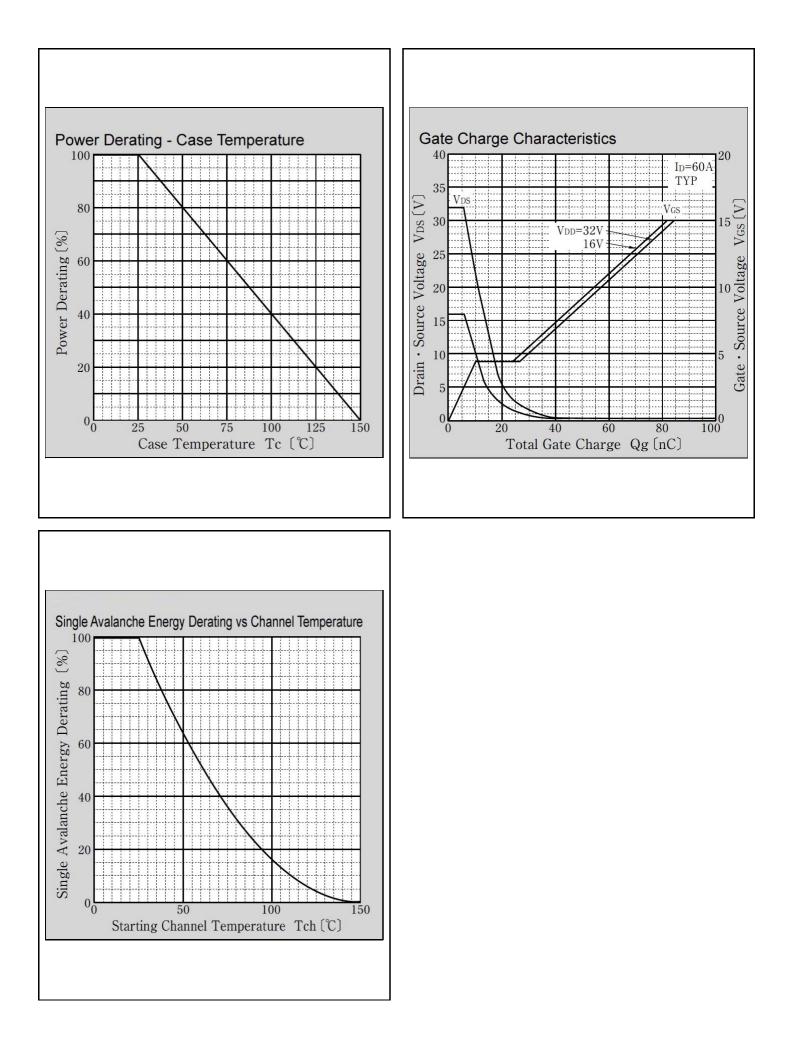
ltom				Ratings			
Item	Symbol	Conditions	MIN	ТҮР	MAX	Unit	
Drain-Source breakdown voltage		ID=1mA, VGS=0V	40			V	
Zero gate voltage drain current I _{DSS}		VDS=40V, VGS=0V			1	μA	
Gate-source leakage current	I _{GSS}	VGS=±20V, VDS=0V			±0.1	μA	
Forward transconductance g _{fs}		ID=30A, VDS=10V	19	38		S	
Static drain-source on-state R _{DS(ON)}		ID=30A, VGS=10V		0.0033	0.0042	Ω	
Static drain-source on-state R _{DS(OI}		ID=30A, VGS=4.5V		0.0046	0.0062	Ω	
Gate threshold voltage Vth		ID=1mA, VDS=10V	1.5	2	2.5	V	
Source-drain diode forward V _{SD}		IS=60A, VGS=0V			1.5	V	
Thermal resistance Rth(j-		Junction to case			2	°C/W	
Total gate charge Qg		VDD=32V, VGS=10V, ID=60A		57		nC	
Gate to source charge Qgs		VDD=32V, VGS=10V, ID=60A		10		nC	
Gate to drain charge Qgd		VDD=32V, VGS=10V, ID=60A		18		nC	
Input capacitance Ciss		VDS=25V, VGS=0V, f=1MHz		2900		pF	
Reverce transfer capacitnce Crss		VDS=25V, VGS=0V, f=1MHz		280		pF	
Output capacitance Coss		VDS=25V, VGS=0V, f=1MHz		500		pF	
Turn-on delay time td(on)		ID=30A, RL=0.67Ω, VDD=20V, Rg=0Ω, VGS(+)=10V, VGS(-)=0V		10		ns	
Rise time	tr	ID=30A, RL=0.67Ω, VDD=20V, Rg=0Ω, VGS(+)=10V, VGS(-)=0V		24		ns	
Turn-off delay time	td(off)	ID=30A, RL=0.67Ω, VDD=20V, Rg=0Ω, VGS(+)=10V, VGS(-)=0V		22		ns	
Fall time	tf	ID=30A, RL=0.67Ω, VDD=20V, Rg=0Ω, VGS(+)=10V, VGS(-)=0V		4		ns	
Diode reverse recovery time	trr	IF=60A, VGS=0V, di/dt=100A/µs		40		ns	
Diode reverse recovery charge	Qrr	IF=60A, VGS=0V, di/dt=100A/µs		47		nC	

* : See the original Specifications

CHARACTERISTIC DIAGRAMS



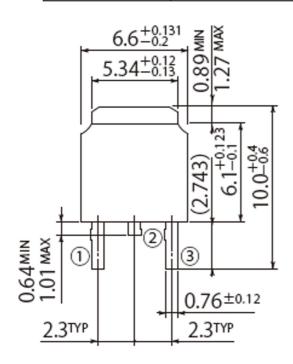


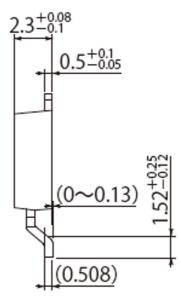


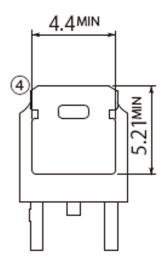
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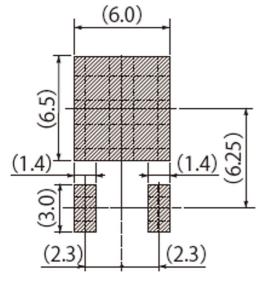
G2

JEDEC Code	TO-252AA
JEITA Code	-
House Name	FB









Referential Soldering Pad

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